

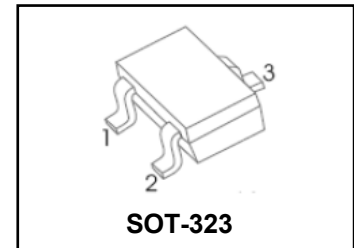
General Purpose Transistors

PNP Silicon

- We declare that the material of product compliance with RoHS requirements.
- **Pb-Free package is available**
 RoHS product for packing code suffix "G"
 Halogen free product for packing code suffix "H"

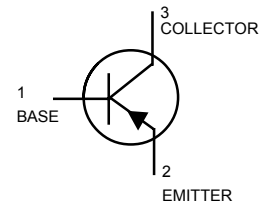
ORDERING INFORMATION

Device	Marking	Shipping
MMBT4403WT1	2T	3000/Tape & Reel



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CE0}	– 40	Vdc
Collector–Base Voltage	V_{CBO}	– 40	Vdc
Emitter–Base Voltage	V_{EBO}	– 5.0	Vdc
Collector Current — Continuous	I_C	– 600	mAdc



THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board $T_A = 25^\circ\text{C}$	P_D	150	mW
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	833	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	–55 to +150	$^\circ\text{C}$

DEVICE MARKING

MMBT4403WT1 = 2T

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage (3) ($I_C = -1.0 \text{ mAdc}, I_E = 0$)	$V_{(BR)CEO}$	– 40	—	Vdc
Collector–Base Breakdown Voltage ($I_C = -0.1 \text{ mAdc}, I_E = 0$)	$V_{(BR)CBO}$	– 40	—	Vdc
Emitter–Base Breakdown Voltage ($I_E = -0.1 \text{ mAdc}, I_C = 0$)	$V_{(BR)EBO}$	– 5.0	—	Vdc
Base Cutoff Current ($V_{CE} = -35 \text{ Vdc}, V_{EB} = -0.4 \text{ Vdc}$)	I_{BEV}	—	– 0.1	μAdc
Collector Cutoff Current ($V_{CE} = -35 \text{ Vdc}, V_{EB} = -0.4 \text{ Vdc}$)	I_{CEX}	—	– 0.1	μAdc

1. FR–5 = 1.0 x 0.75 x 0.062 in.
2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.
3. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$; Duty Cycle $\leq 2.0\%$.



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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS				
DC Current Gain (I _C = -0.1 mA, V _{CE} = -1.0 Vdc)	h _{FE}	30	—	—
(I _C = -1.0 mA, V _{CE} = -1.0 Vdc)		60	—	
(I _C = -10 mA, V _{CE} = -1.0 Vdc)		100	—	
(I _C = -150 mA, V _{CE} = -2.0 Vdc)(3)		100	300	
(I _C = -500 mA, V _{CE} = -2.0 Vdc)(3)		20	—	
Collector-Emitter Saturation Voltage(3) (I _C = -150mA, I _B = -15 mA)	V _{CE(sat)}	—	-0.4	Vdc
(I _C = -500 mA, I _B = -50 mA)		—	-0.75	
Base-Emitter Saturation Voltage (3) (I _C = -150 mA, I _B = -15 mA)	V _{BE(sat)}	-0.75	-0.95	Vdc
(I _C = -500 mA, I _B = -50 mA)		—	-1.3	

SMALL-SIGNAL CHARACTERISTICS

Current-Gain — Bandwidth Product (I _C = -20mA, V _{CE} = -10 Vdc, f = 100 MHz)	f _T	200	—	MHz
Collector-Base Capacitance (V _{CB} = -10 Vdc, I _E = 0, f = 1.0 MHz)	C _{cb}	—	8.5	pF
Emitter-Base Capacitance (V _{BE} = -0.5 Vdc, I _C = 0, f = 1.0 MHz)	C _{eb}	—	30	pF
Input Impedance (V _{CE} = -10 Vdc, I _C = -1.0 mA, f = 1.0 kHz)	h _{ie}	1.5	15	kΩ
Voltage Feedback Ratio (V _{CE} = -10 Vdc, I _C = -1.0 mA, f = 1.0 kHz)	h _{re}	0.1	8.0	X 10 ⁻⁴
Small-Signal Current Gain (V _{CE} = -10 Vdc, I _C = -1.0 mA, f = 1.0 kHz)	h _{fe}	60	500	—
Output Admittance (V _{CE} = -10 Vdc, I _C = -1.0 mA, f = 1.0 kHz)	h _{oe}	1.0	100	μmhos

SWITCHING CHARACTERISTICS

Delay Time	(V _{CC} = -30 Vdc, V _{EB} = -2.0 Vdc, I _C = -150mA, I _{B1} = -15 mA)	t _d	—	15	ns
Rise Time		t _r	—	20	
Storage Time	(V _{CC} = -30 Vdc, I _C = -150 mA, I _{B1} = I _{B2} = -15 mA)	t _s	—	225	ns
Fall Time		t _f	—	30	

3. Pulse Test: Pulse Width ≤300 μs; Duty Cycle ≤2.0%.

SWITCHING TIME EQUIVALENT TEST CIRCUITS

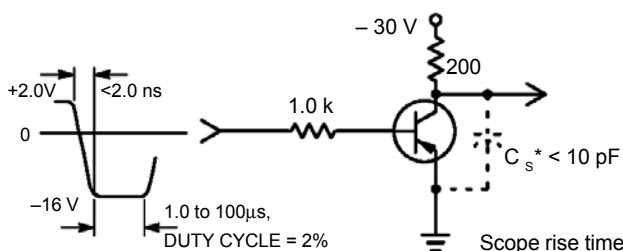


Figure 1. Turn-On Time

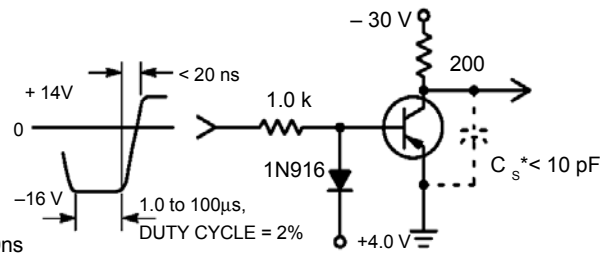


Figure 2. Turn-Off Time

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TYPICAL TRANSIENT CHARACTERISTICS

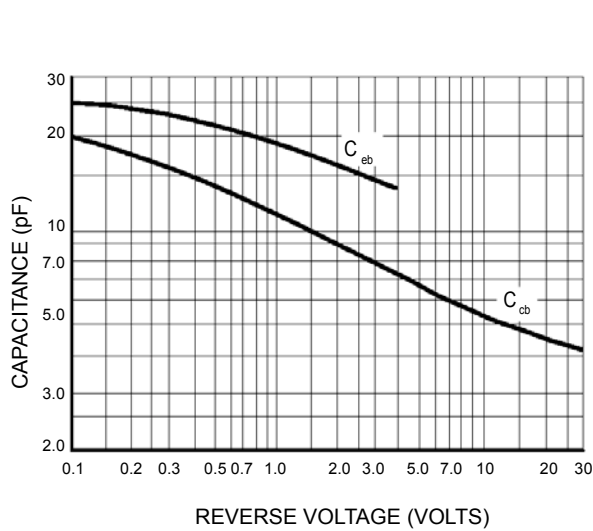


Figure 3. Capacitance

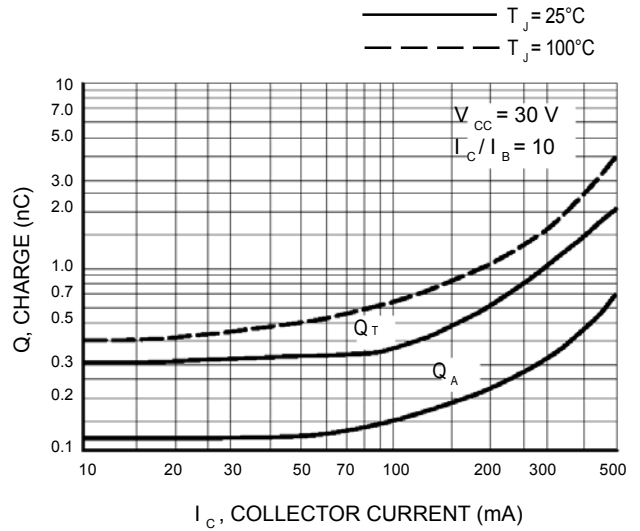


Figure 4. Charge Data

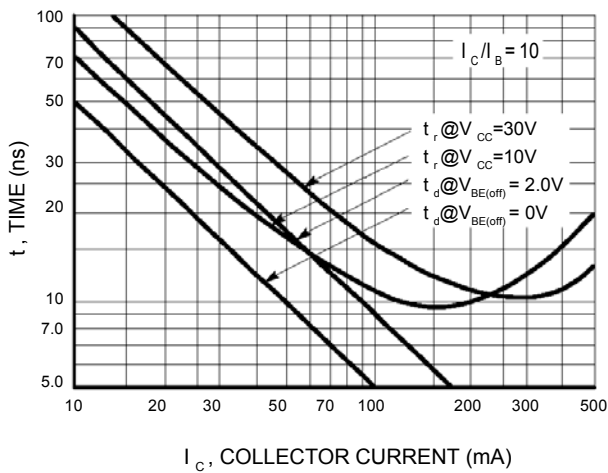


Figure 5. Turn-On Time

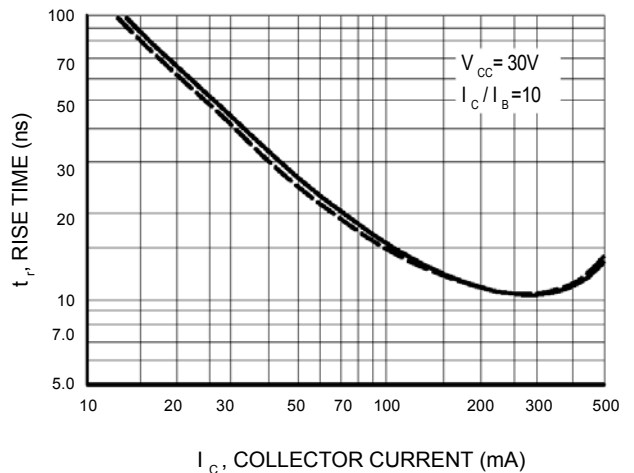


Figure 6. Rise Time

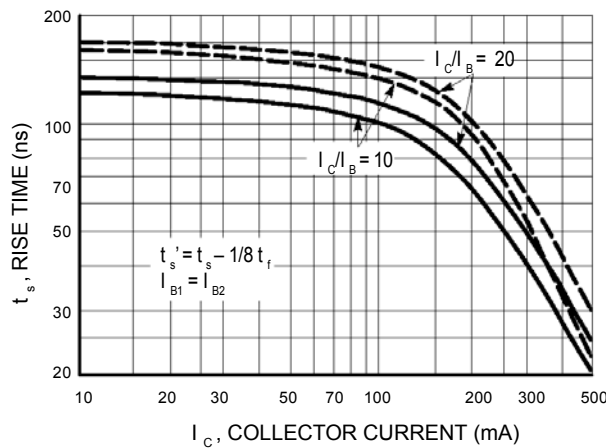


Figure 7. Storage Time



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SMALL-SIGNAL CHARACTERISTICS

NOISE FIGURE

$V_{CE} = -10 \text{ Vdc}$, $T_A = 25^\circ\text{C}$

Bandwidth = 1.0 Hz

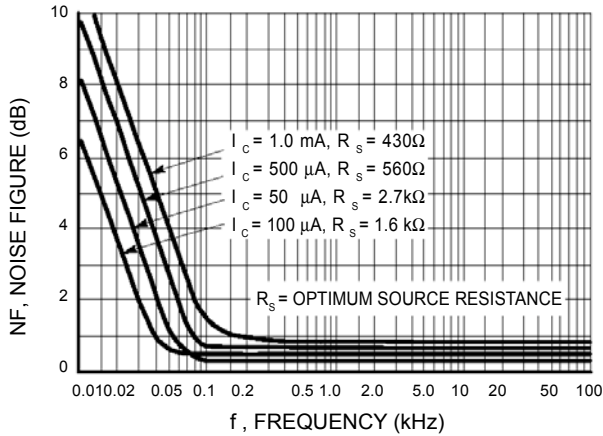


Figure 8. Frequency Effects

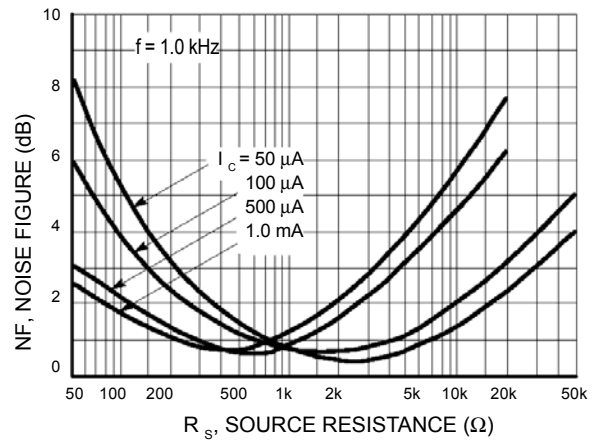


Figure 9. Source Resistance Effects

h PARAMETERS

($V_{CE} = -10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$, $T_A = 25^\circ\text{C}$)

This group of graphs illustrates the relationship between h_{fe} and other "h" parameters for this series of transistors. To obtain these curves, a high-gain and a low-gain unit were selected from the MMBT4403WT1 lines, and the same units were used to develop the correspondingly numbered curves on each graph.

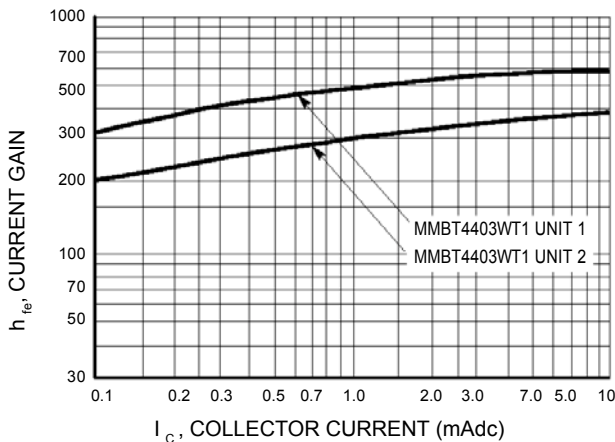


Figure 10. Current Gain

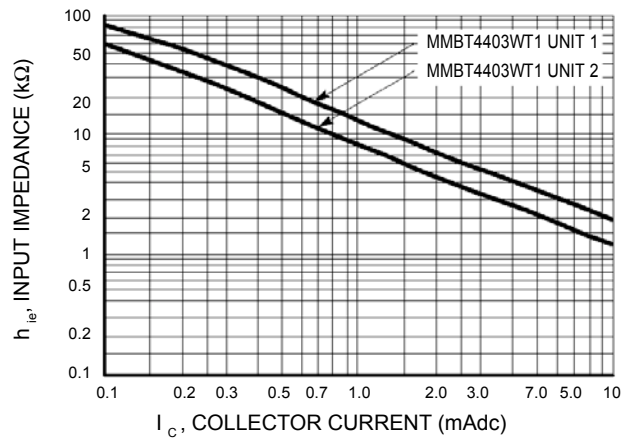


Figure 11. Input Impedance

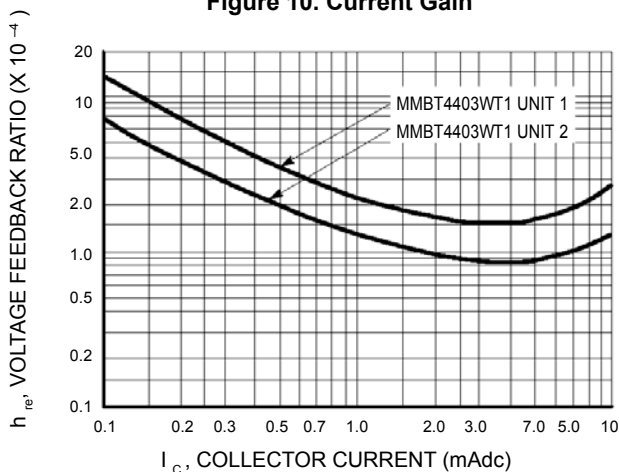


Figure 12. Voltage Feedback Ratio

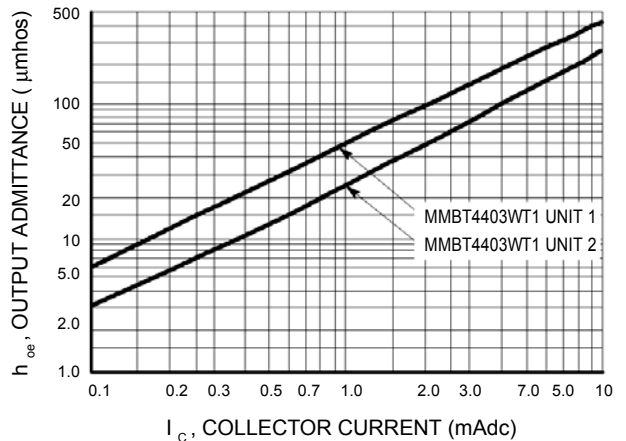


Figure 13. Output Admittance



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STATIC CHARACTERISTICS

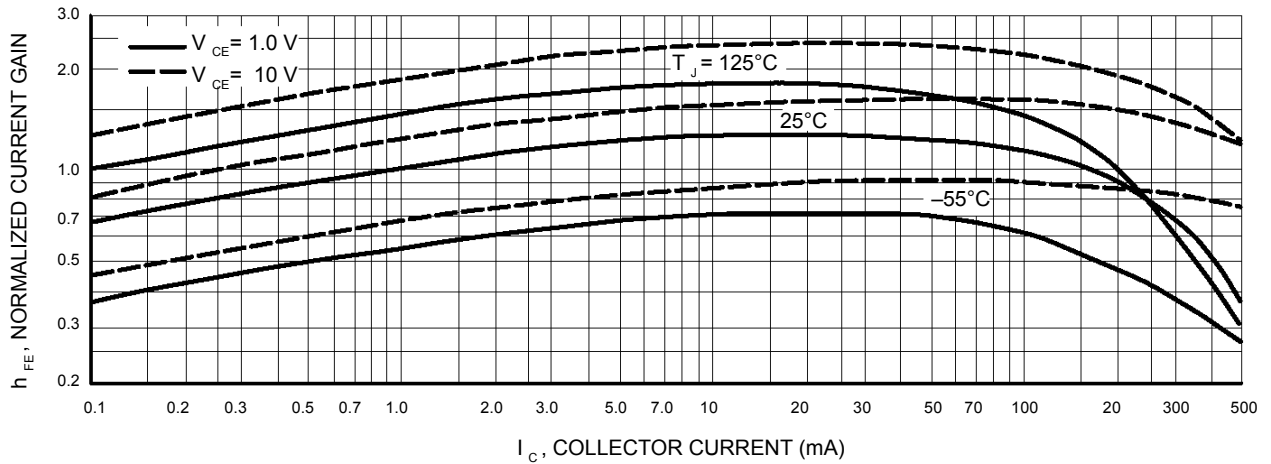


Figure 14. DC Current Gain

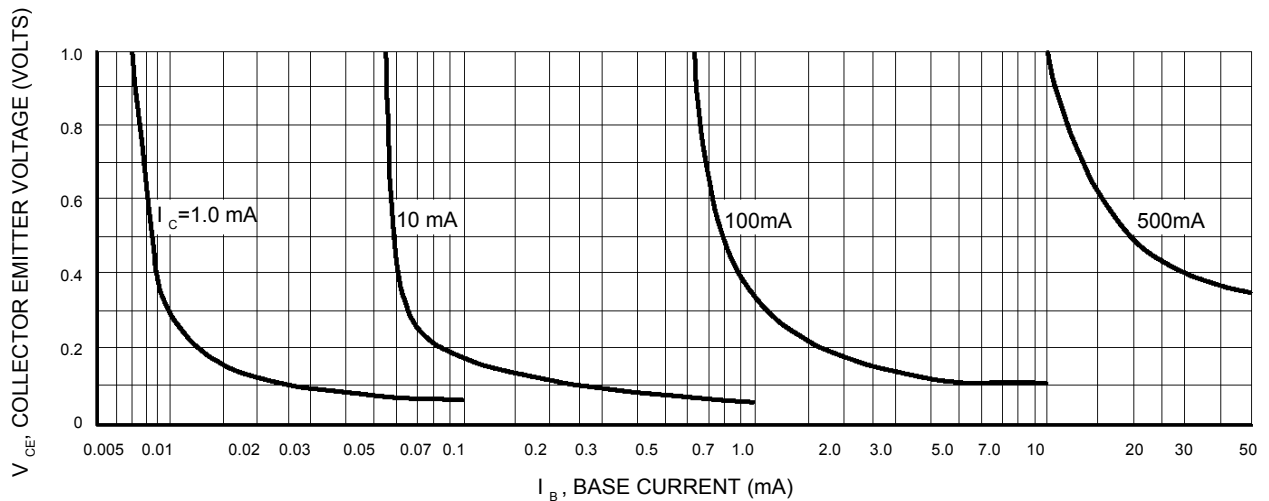


Figure 15. Collector Saturation Region

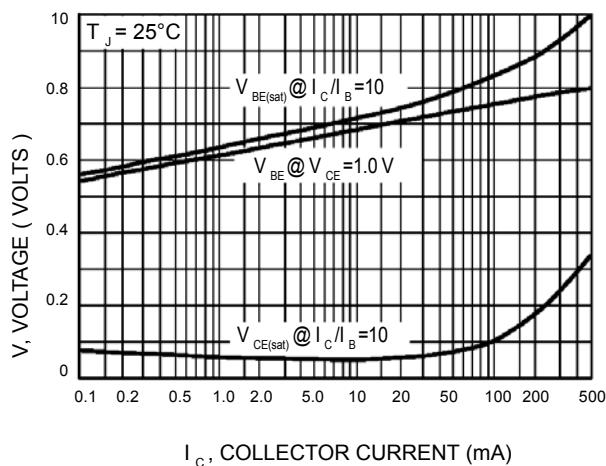


Figure 16. "On" Voltages

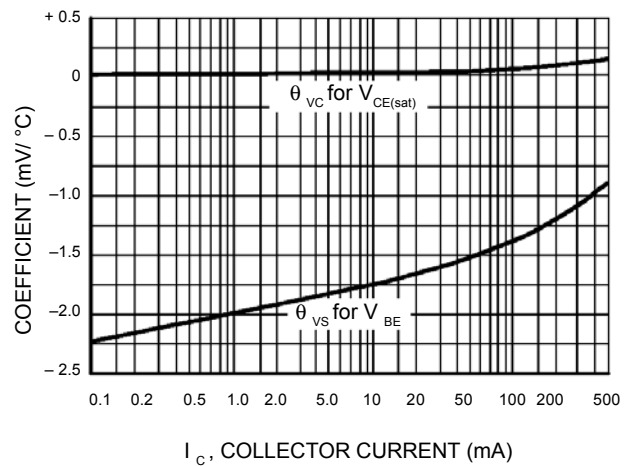
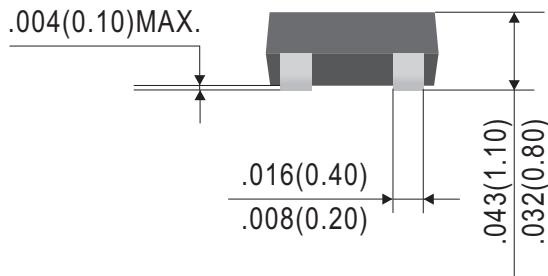
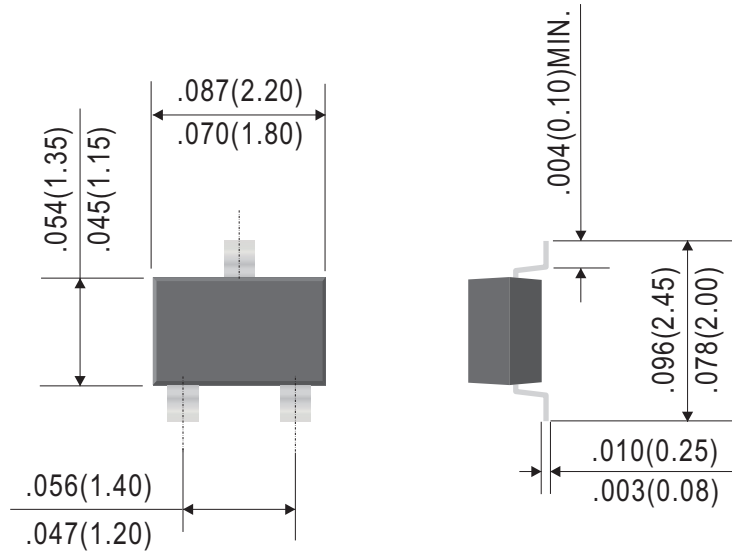


Figure 17. Temperature Coefficients

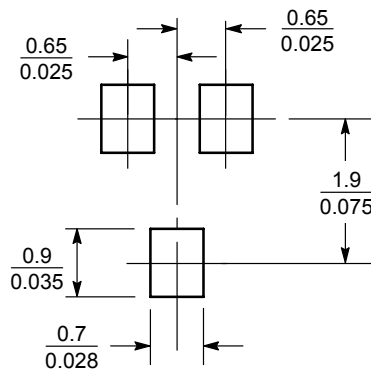
General Purpose Transistors

SOT-323



Dimensions in inches and (millimeters)

SOLDERING FOOTPRINT*



SCALE 10:1 $\left(\frac{\text{mm}}{\text{inches}}\right)$